

# Claims

- [c1] 1.A semiconductor device, comprising:  
a first implant region having a first conductivity type;  
and  
a second implant region having a second conductivity type;  
wherein said first and said second implant regions are self-aligned with respect to one another.
- [c2] 2.The semiconductor device of claim 1, wherein said first implant region is formed following a lithographic patterning step and said second implant region is formed following a non-lithographic, image reversal step.